



# 20A, 100V - 200V Schottky Barrier Rectifier

#### **FEATURES**

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

#### **MECHANICAL DATA**

• Case: ITO-220AB

Molding compound meets UL 94V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

Mounting torque: 0.56 N·m maximum
Meet JESD 201 class 2 whisker test

Polarity: As marked

• Weight: 1.70g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F</sub>	20	Α		
$V_{RRM}$	100 - 200	V		
I <sub>FSM</sub>	150	Α		
T <sub>J MAX</sub>	175	°C		
Package	ITO-220AB			
Configuration	Dual dies			

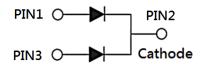








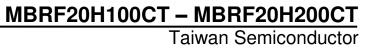
#### ITO-220AB



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	MBRF MBRF 20H100CT 20H150CT		MBRF 20H200CT	UNIT	
Marking code on the device		MBRF 20H100CT	MBRF 20H150CT	MBRF 20H200CT		
Repetitive peak reverse voltage	$V_{RRM}$	100	150	200	V	
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	70	105	140	V	
Forward current	I <sub>F</sub>	20		Α		
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	150			А	
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1.0 0.5		0.5	Α	
Peak repetitive forward current (Rated V <sub>R</sub> , Square wave, 20KHz)	I <sub>FRM</sub>	20		А		
Critical rate of rise of off-state voltage	dv/dt	10,000		V/µs		
Junction temperature	TJ	-55 to +175		°C		
Storage temperature	T <sub>STG</sub>	-55 to +175			°C	

#### Notes:

1.  $tp = 2.0\mu s$ , 1.0KHz





THERMAL PERFORMANCE					
PARAMETER	SYMBOL	TYP	UNIT		
Junction-to-case thermal resistance	R <sub>eJC</sub>	3.5	°C/W		

ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
Forward voltage per diode <sup>(1)</sup>	MBRF20H100CT	I <sub>F</sub> = 10A,T <sub>J</sub> = 25°C	V <sub>F</sub>	-	0.85	V
	MBRF20H150CT				0.88	V
	MBRF20H200CT				0.00	V
	MBRF20H100CT			1	0.95	V
	MBRF20H150CT	I <sub>F</sub> = 20A,T <sub>J</sub> = 25°C		ı	0.97	V
	MBRF20H200CT					
	MBRF20H100CT	I <sub>F</sub> = 10A,T <sub>J</sub> = 125°C		-	0.75	V
	MBRF20H150CT					
	MBRF20H200CT					
	MBRF20H100CT					
	MBRF20H150CT	$I_F = 20A, T_J = 125$ °C		-	0.85	V
	MBRF20H200CT					
Reverse current @ rated V <sub>R</sub> per diode <sup>(2)</sup>		T <sub>J</sub> = 25°C	I <sub>R</sub>	-	5	μΑ
		T <sub>J</sub> = 125°C	I <sub>R</sub>	-	2	mA

## Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION					
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING			
MBRF20HxCT	ITO-220AB	50 / Tube			
MBRF20HxCTH	ITO-220AB	50 / Tube			

## Notes:

- 1. "x" defines voltage from 100V(MBRF20H100CT) to 200V(MBRF20H200CT)
- 2. "H" means AEC-Q101 qualified

Fig.2 Typical Junction Capacitance



### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

**Fig.1 Forward Current Derating Curve** 

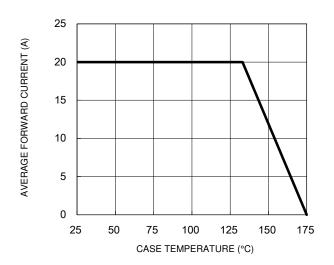
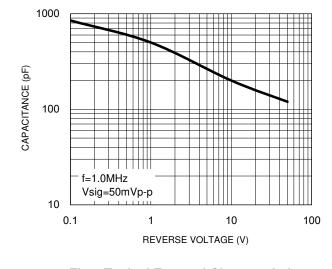
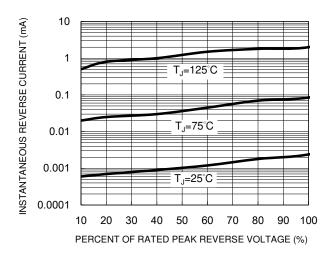


Fig.3 Typical Reverse Characteristics



**Fig.4 Typical Forward Characteristics** 



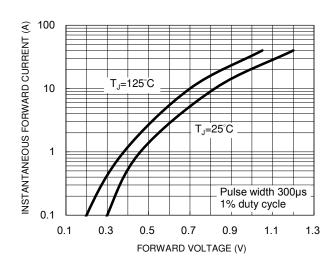
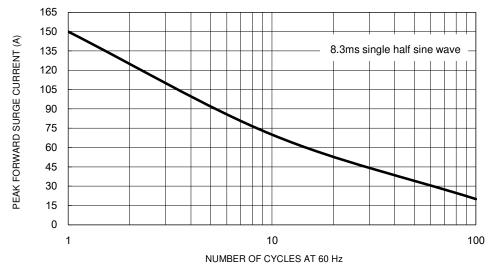


Fig.5 Maximum Non-Repetitive Forward Surge Current



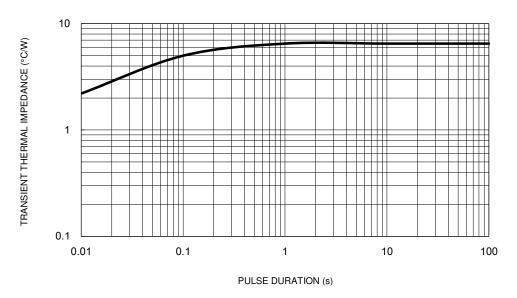
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 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

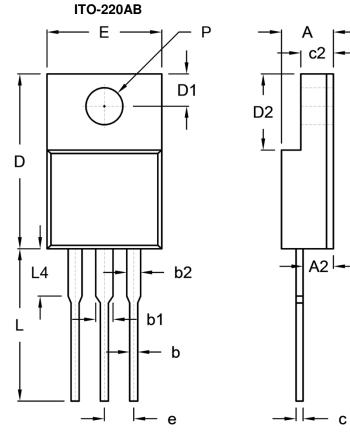
Fig.6 Typical Transient Thermal Impedance





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## **PACKAGE OUTLINE DIMENSIONS**



DIM.	Unit	(mm)	Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
Α	4.30	4.70	0.169	0.185	
A2	2.30	2.96	0.091	0.117	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
С	0.46	0.76	0.018	0.030	
c2	2.50	3.16	0.098	0.124	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
E	9.60	10.30	0.378	0.406	
е	2.41	2.67	0.095	0.105	
L	12.60	13.80	0.496	0.543	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

## **MARKING DIAGRAM**



P/N = Marking Code = Green Compound G

YWW = Date Code = Factory Code



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